

Nano-Thermoelectric Devices Fabricated by Ion Beam Writing

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14. ABSTRACT A lithographic process has been developed to construct the suspended structure. The self-heating 3W method and measurement systems for nanoscale material have been constructed. The thermal conductivity and specific heat of diameter of 180nm nickel wire are 23 W/m-K and 64.6 J/mol-K (at 25C), respectively. A 30 nano-wire has been fabricated for concept demonstration.					
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Nanotechnology and Energy

Improved efficiency of energy usage:

- Non-thermal energy usage, via nanostructured devices such as fuel cells;
- Molecularly tailored catalysts, for heightened selectivity and byproduct elimination;
- High-strength materials, which will decrease transportation costs;
- Electricity storage and electrosynthesis, both for portable power sources, and for chemical fuel generation;
- Distributed fabrication, to minimize transportation infrastructure.

Information-intensive energy extraction:

- Extensive real-time sensing, for better conventional resource extraction;
- Cheap nanofabrication, which will make practical distributed collection from diffuse sources, as well as better energy management through such devices as "smart windows" and non-thermal light sources

Nanotechnology and Energy

Solid-state energy generation:

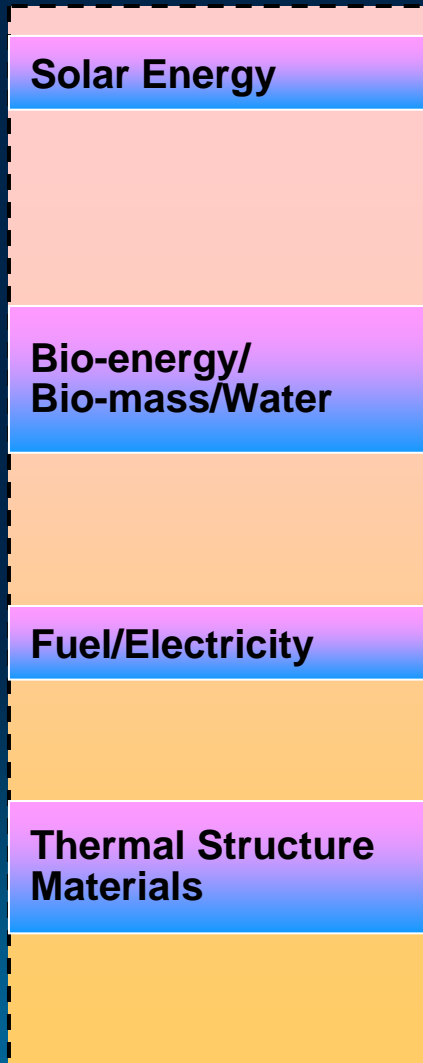
- Solar power, via photovoltaics and artificial photosynthesis;
- Thermoelectric conversion, the direct solid-state transformation of thermal gradients into electricity;
- Piezoelectric conversion, for direct conversion of mechanical energy into electricity.
- Solid electrolytes—critical in fuel cells and supercapacitors; relevant to intercalation batteries, smart windows, electrocatalysis, and also to ionic separation.

Nanoscale structuring at an interface is fundamental to many applications, including:

- Catalyst surfaces;
- Large-area semiconductor p-n junctions, critical to thermoelectric and photovoltaic materials;
- Nanolayered structures, such as for high-performance capacitors, thermoelectric materials, multijunction photovoltaics, piezoelectric stacks, and sensitized photosynthetic materials.

Nanotechnology and Energy System

Energy Source/Materials



Critical Nanotechnology

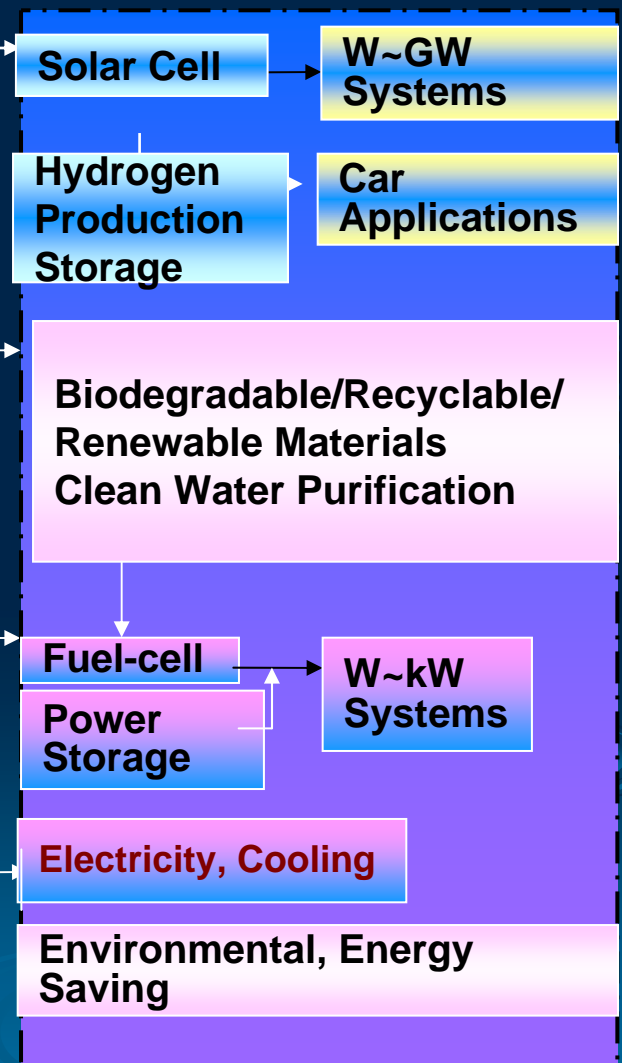
Full spectrum nanomaterials
Printable /Flexible material
& substrate
Nano-scale crystalline
silicon

Bio-catalyst / Biodegradable
Chirality centered material
Functional Nano-fibers

High active Bio-fuel
Nano Structural Materails for
catalyst
Nanostructural
Organic/Inorganic Materials
Hyper-branch catalyst
Organic/Inorganic
electrolyte

Nanostructure Low
Phonon scattering, high
ZT Materials
Surface Plasmon
Quantum well design

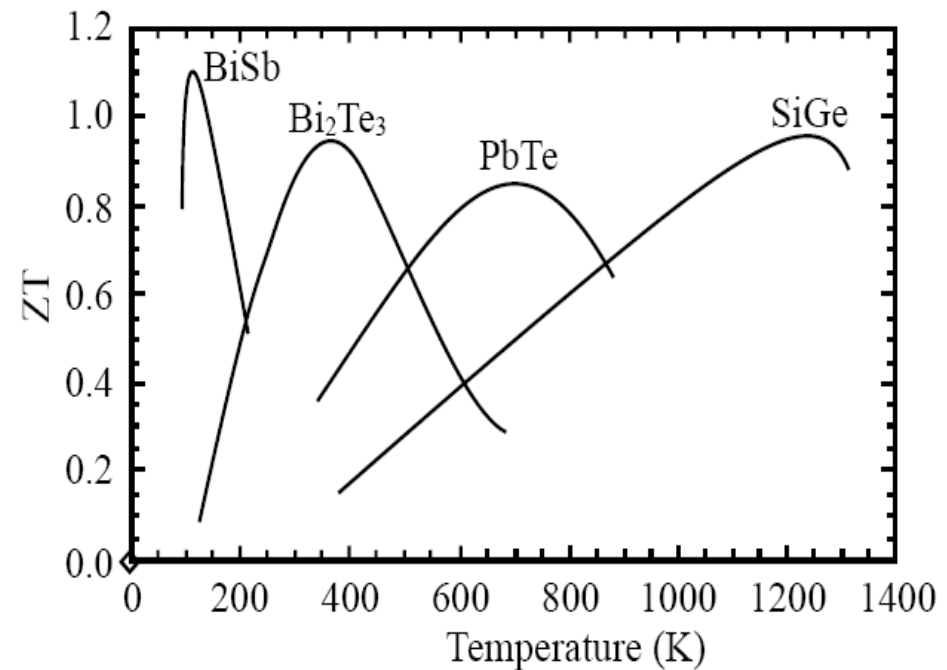
System Platform



* **Energy conversion efficiency** **Figure of Merit $\square ZT$**

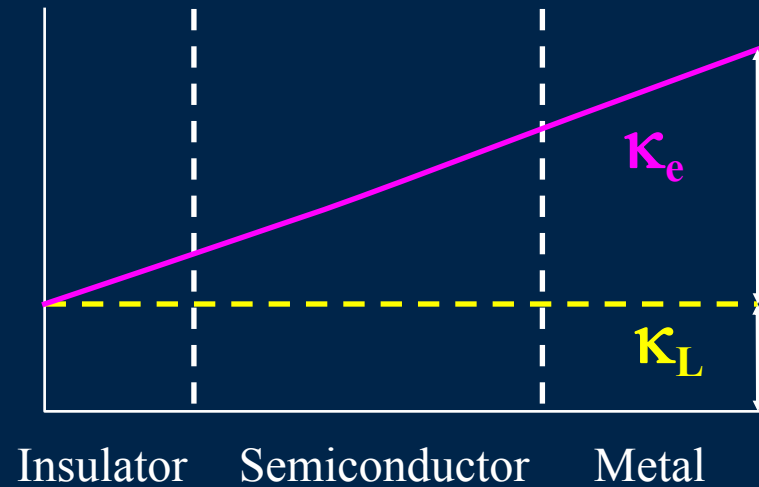
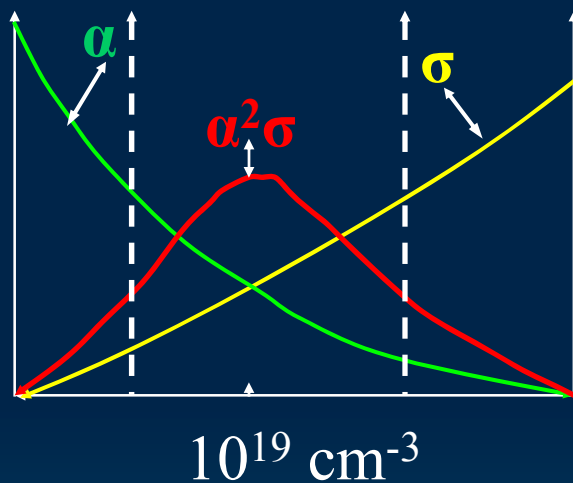
$$ZT = \frac{\alpha^2 \sigma T}{(\kappa_E + \kappa_L)}$$

α is Seebeck Coefficient.
 σ is Electric Conductivity.
 κ is Thermal Conductivity
 T absolute temperature



$$ZT = \frac{\alpha^2 \sigma T}{(\kappa_E + \kappa_L)}$$

* How to increase ZT ?



α, σ ($D(\epsilon)$, ϵ_F, μ)

$\sigma / \kappa_e = 1 / (L_0 T)$
Wiedmann-Franz Law:
 $L_0 \square$ Lorentz num.

Reduce phonon thermal conductivity

Strategy

1. Increase Seebeck Coefficient α \square quantum size effects,

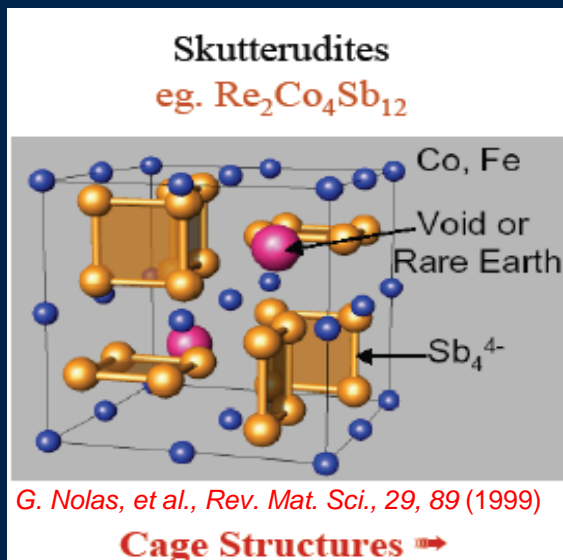
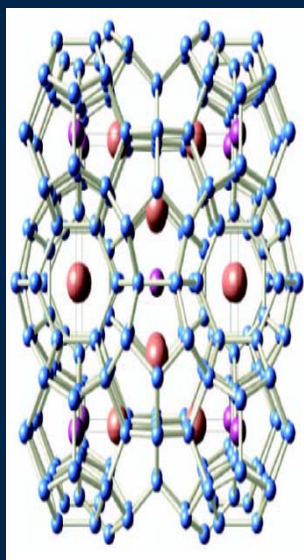
Example: Quantum Wires in Nanostructures

2. Reduce thermal conductivity κ_L \square decrease lattice phonons mean free path.

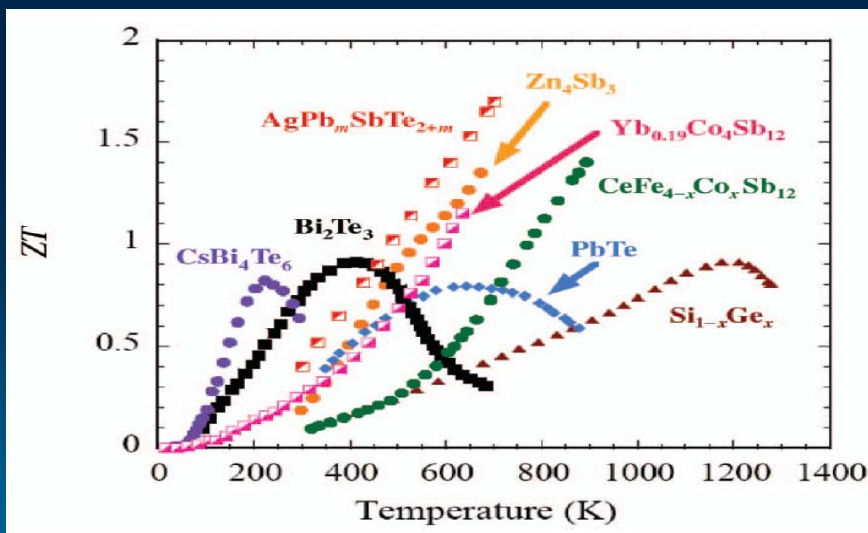
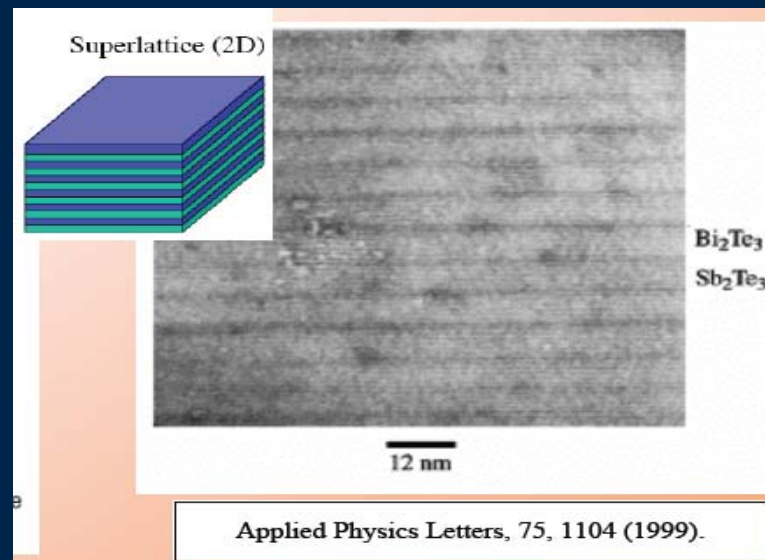
Example: Multilayers or Superlattice , Nanostructured bulk materials (nanoparticle-dispersed composites)

3. Directional dependent of thermal conductivity

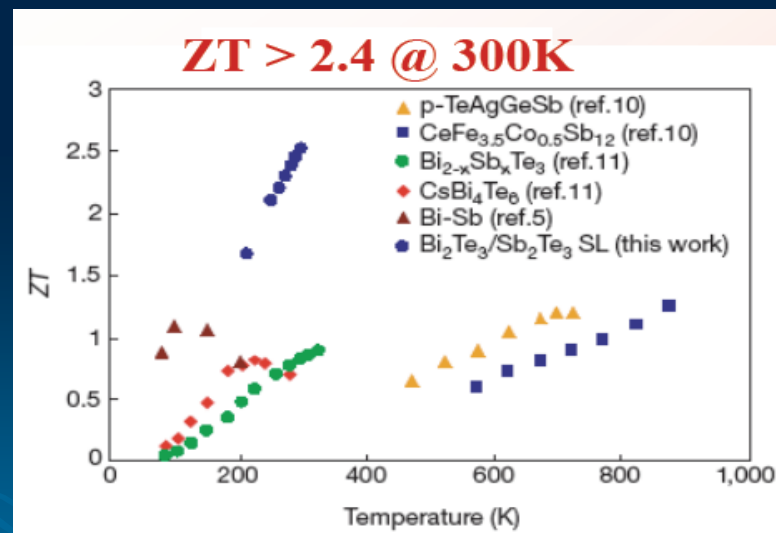
(A) Crystal Structures with “Rattlers”



(B) Superlattice Lattices

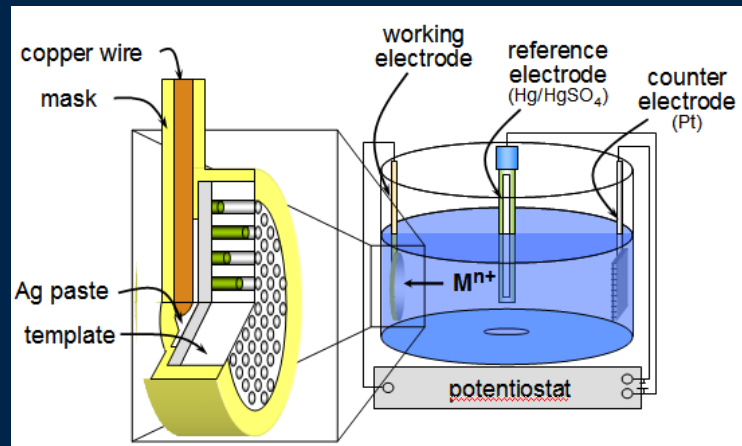


Need higher ZT ~1.5-2

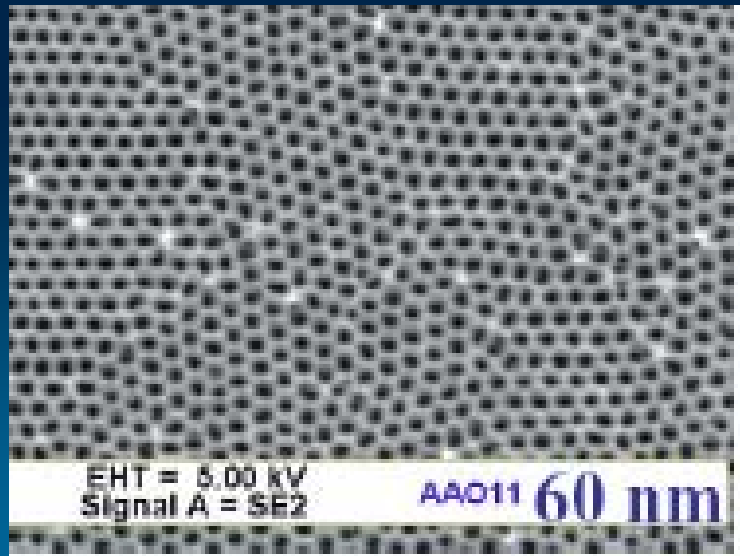


Too thin and too expensive

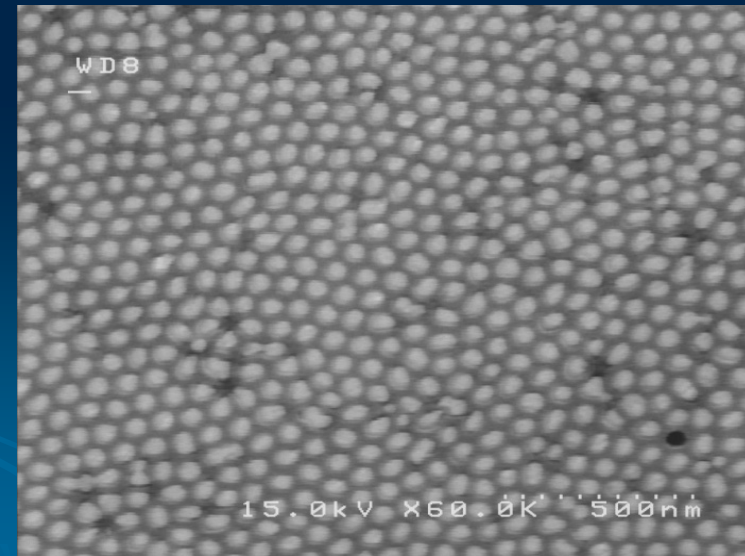
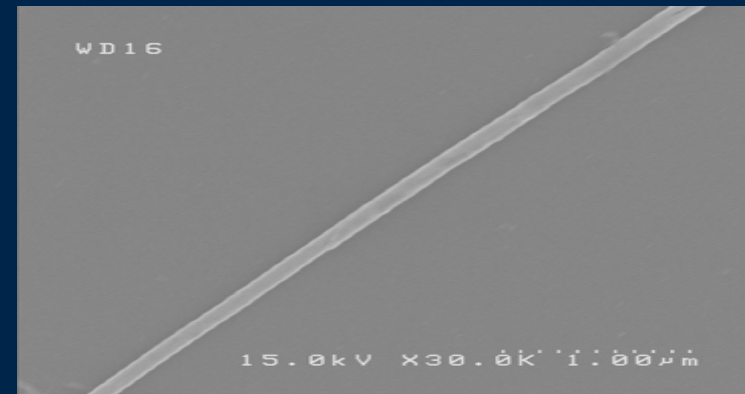
Enhancement of ZT in Nanowire Array



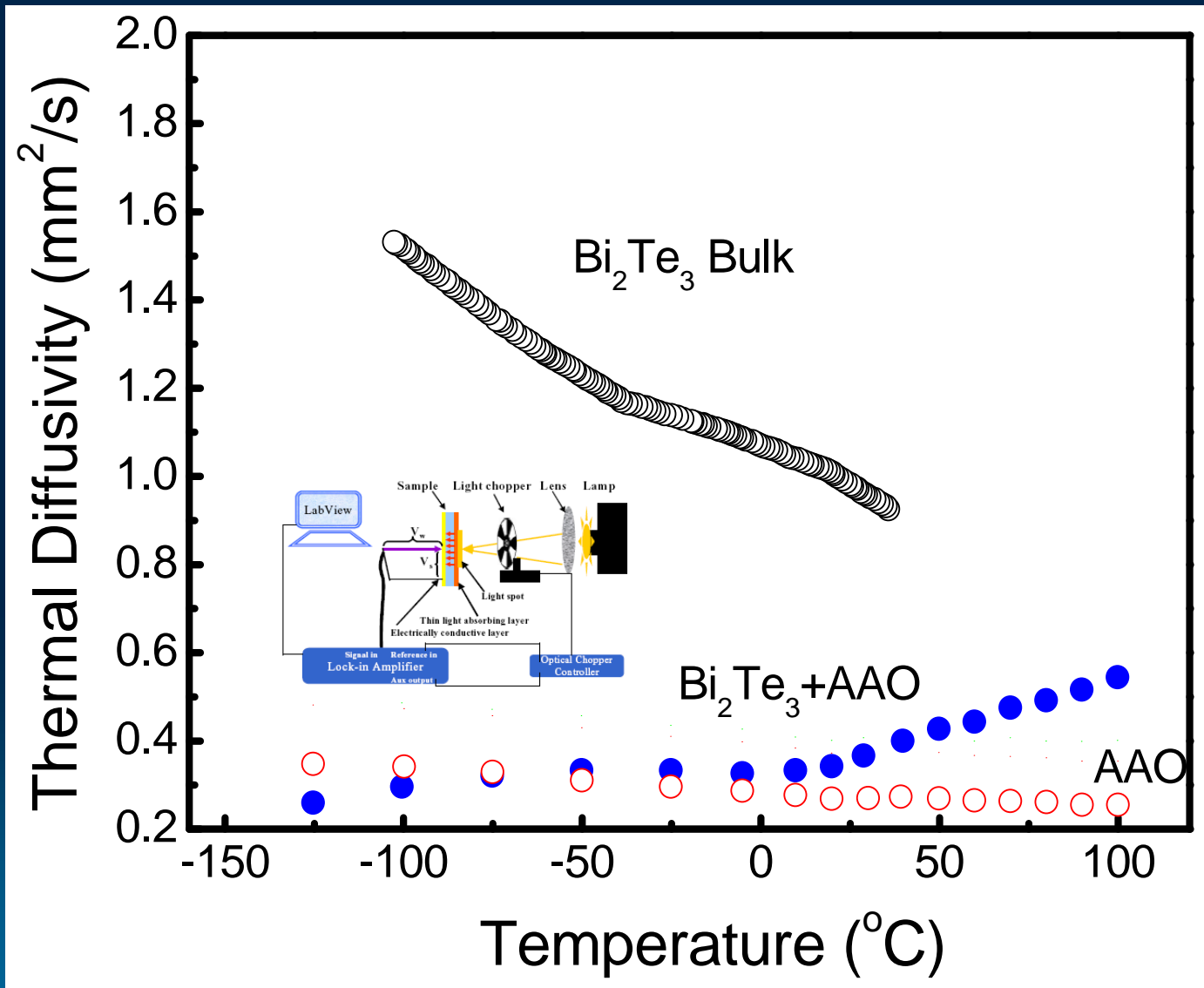
Anodic Aluminum Oxide (AAO)



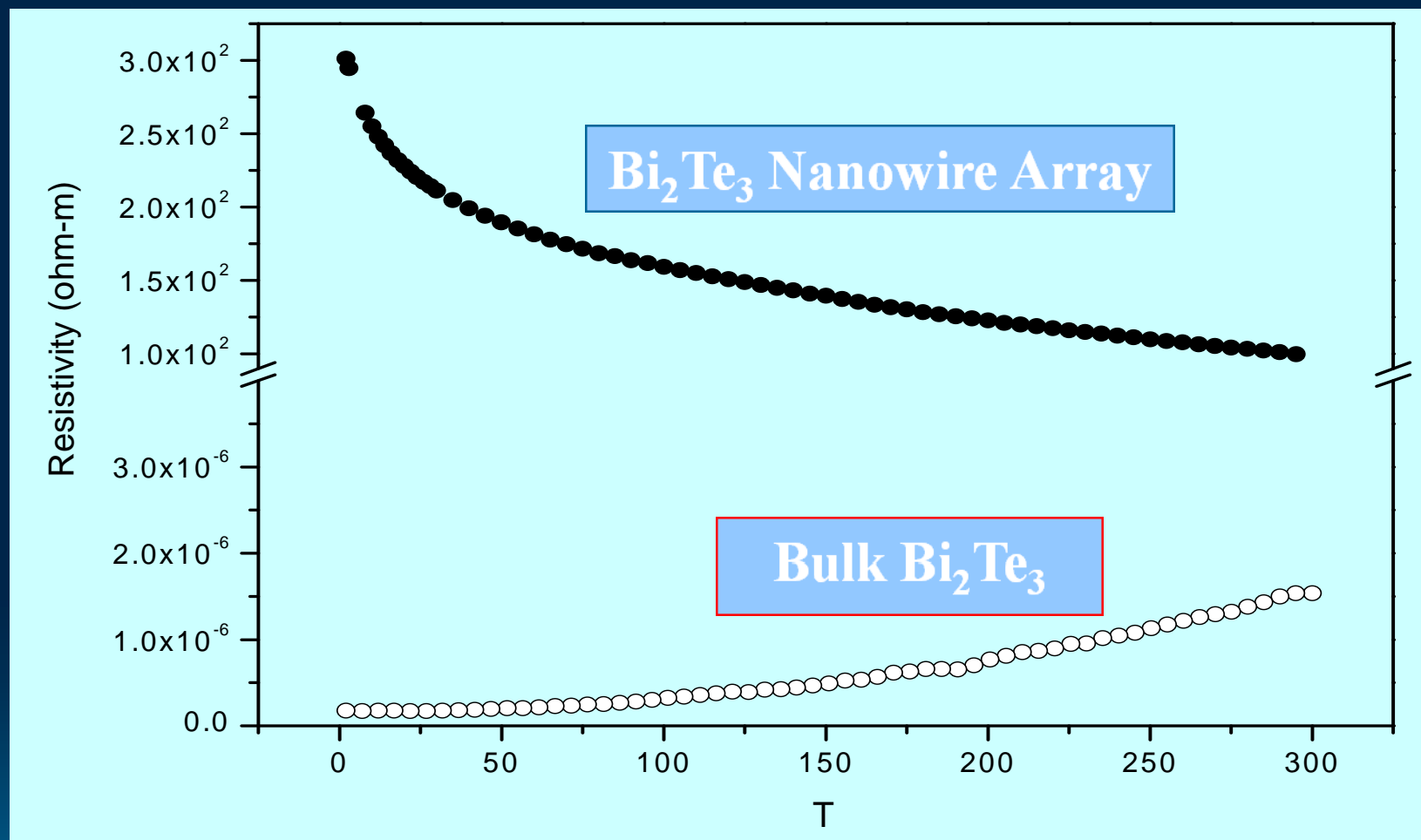
~50 nm Bi₂Te₃
Nanowire array



Thermal Diffusivity of Bi_2Te_3 Bulk and Nanoarray



Resistivity of Bi_2Te_3 Bulk and Nanowire Array



Need to overcome the large resistivity !!
Better quality sample ?

Action Plan

- Nanometer Bi_2Te_3 nanowires fabricated by ion-milling creating “neck” diameters close to the mean free path will be examined using the 3ω process to determine the effect of nanowire diameter on thermal conductivity properties.
- Quantifying the change in heat conduction experimentally in variable diameters provides insight to the theorized mechanisms of thermoelectric performance enhancement and advances designing practical nanothermoelectric devices.
- Experimentally study phonon heat conduction in Ion Milled Bi_2Te_3 Nanowires and 2 dimensional tapered structures to investigate significant performance advance attributed to decreasing heat conduction by phonons – without significant alterations of resistance properties.

Experimental Details—Nanowires

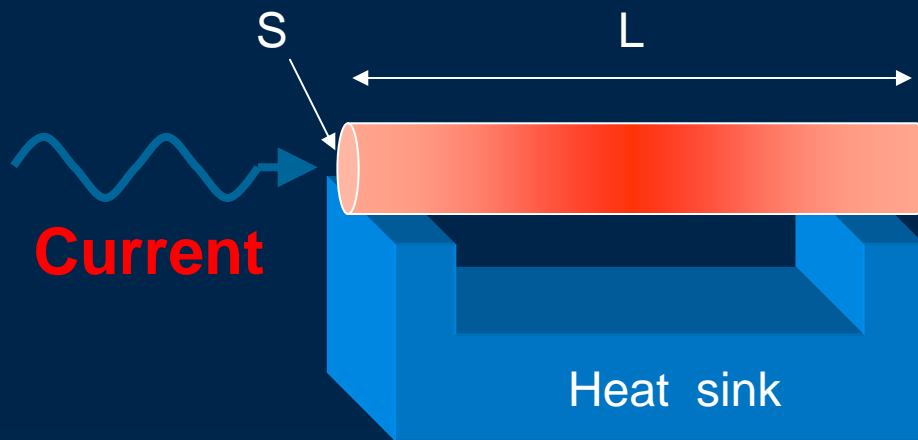
- Fabrication of one individual & suspending nickel nanowire
 - Evaporation deposition
 - E-beam lithography
 - Anisotropic Wet-Etching
- Observation for nano-scale materials
 - 3ω method
 - Electrical conductivity
 - Thermal conductivity
 - Specific heat

Self heating 3ω Method

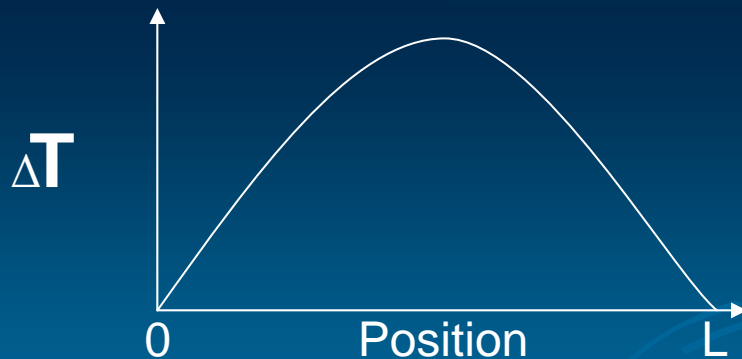
- The basic idea of the 3ω self-heating method is that when one passes an ***alternating current*** with frequency ω , it will heat the wire uniformly.
- If we make a suspension structure, as shown in the next slide, i.e., a uniform wire lies on a high thermal conductive substrate so that the ends part are contacted with substrate but middle part is not.
- It then created a temperature distribution, which with highest temperature rising at mid point and lowest at end point.
- The responded 1st harmonic signal gives the information of electrical conductivity, and 3rd harmonic term the temperature variation.
- Thus, parameter κ and specific heat C_p can be determined by fitting the signal of 3ω voltage with the formula.

Idea of self heating 3ω Method

$$\rho C_p \frac{\partial}{\partial t} T(x, t) - \kappa \frac{\partial^2}{\partial x^2} T(x, t) = \frac{I_0^2 \sin^2 \omega t}{LS} (R + R'(T(x, t)) - T_0)$$



ρ	density
C_p	specific heat
κ	thermal conductivity
L, S	dimension of specimen
R	Resistance
γ	time constant



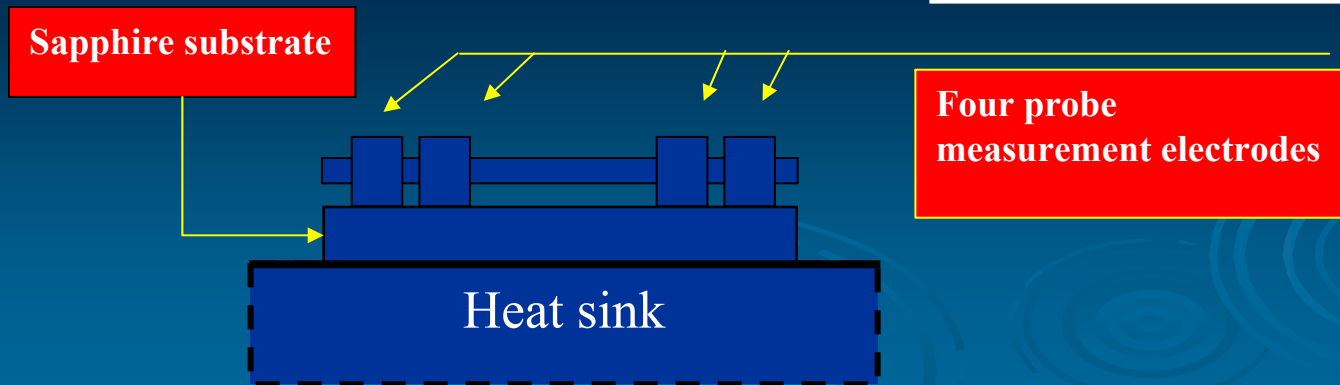
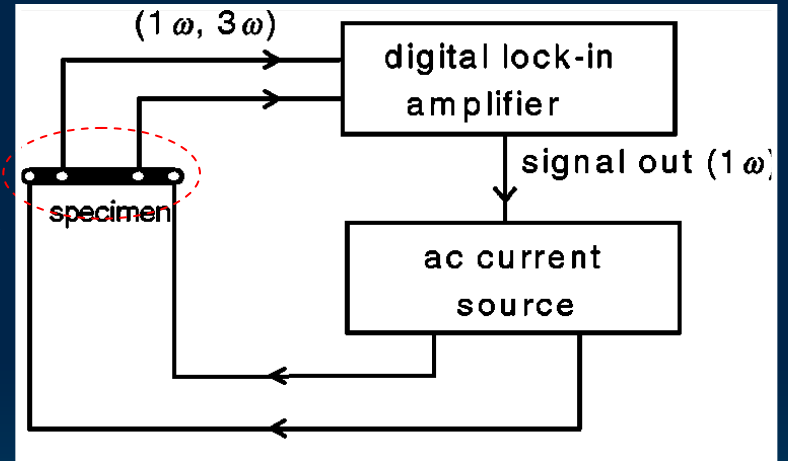
$$V_{3\omega}(t) \approx - \frac{2I_0^3 L R R'}{\pi^4 \kappa S \sqrt{1 + (2\omega\gamma)^2}} \sin(3\omega t - \phi),$$

$$C_p = \pi^2 \gamma \kappa / \rho L^2$$

3^ω Method

- To construct a measurement system of thermodynamic parameters for nanoscale specimen.

1. *Suspended*
2. *Highly thermal conductive to heat sink*
3. *minimize the heat loss*

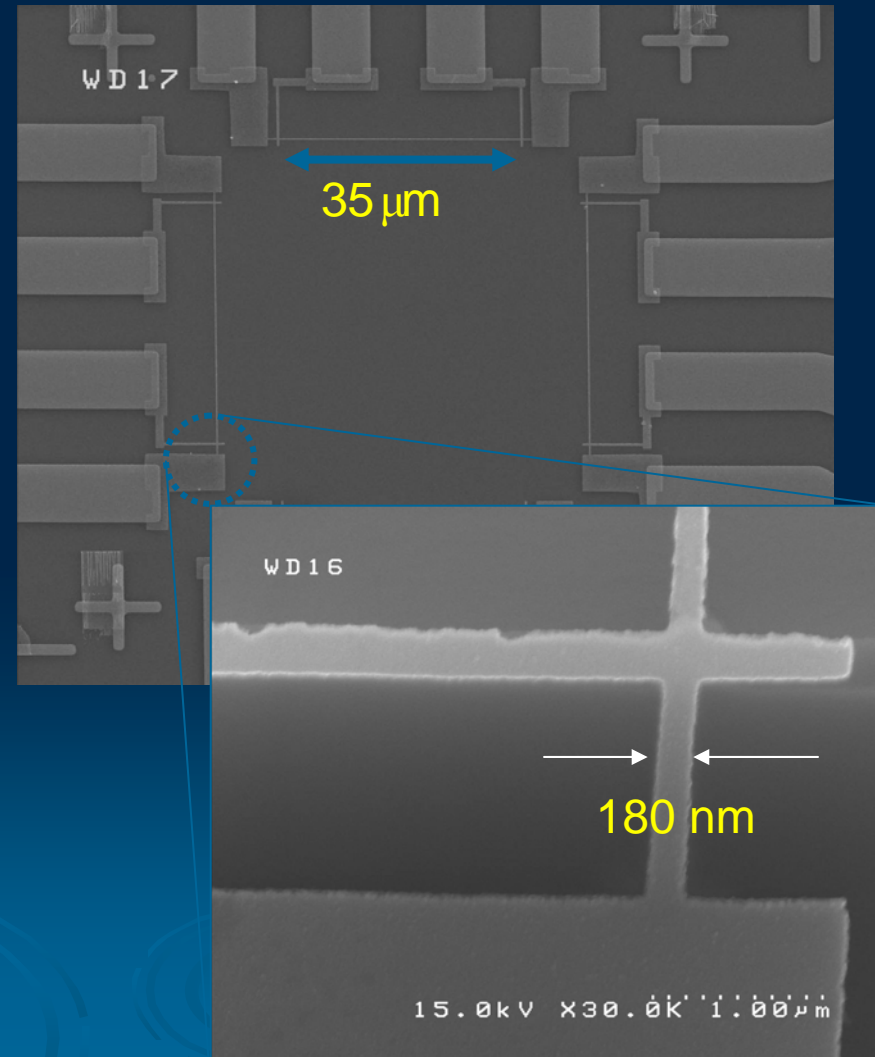
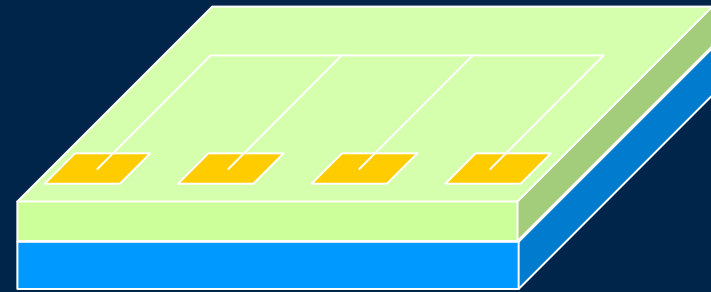
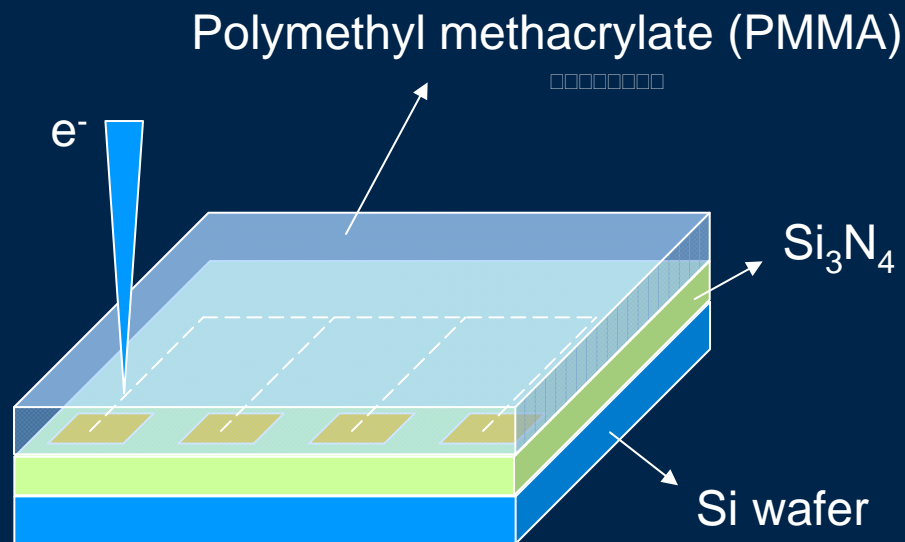


Fabrication of Individual Nanowire—Nickel

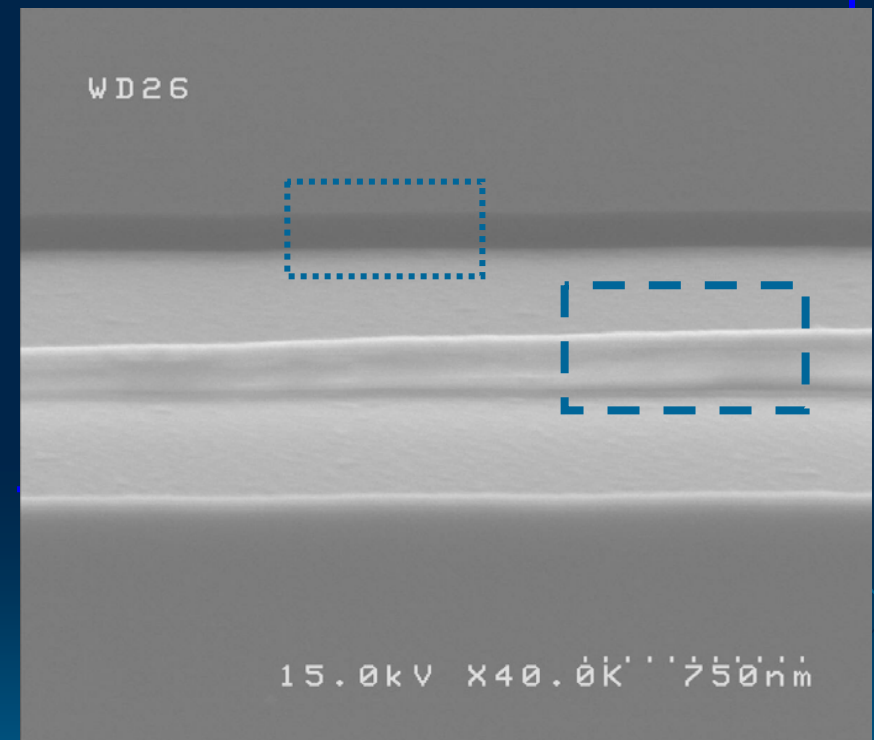
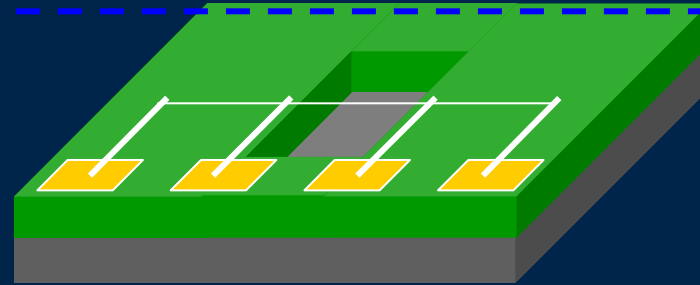
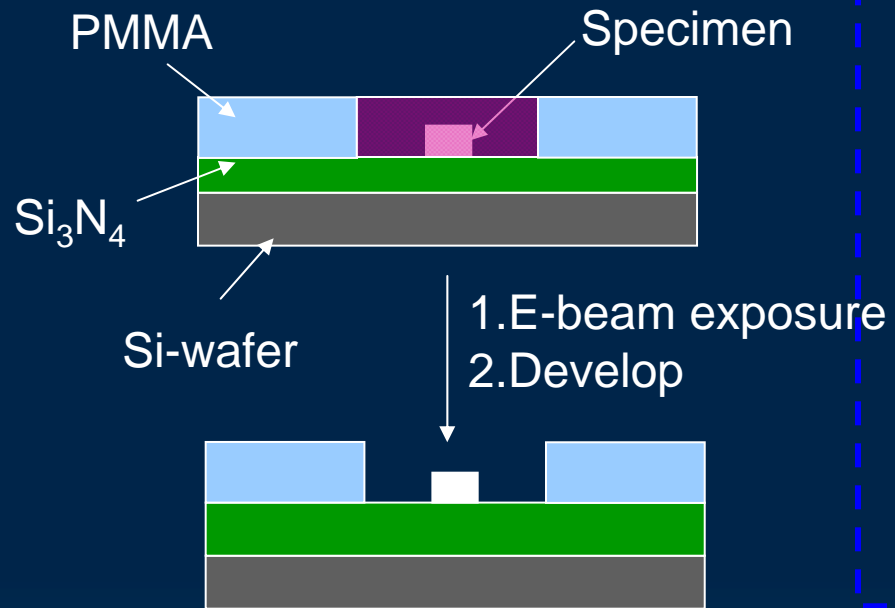
E-beam lithography & evaporate deposition



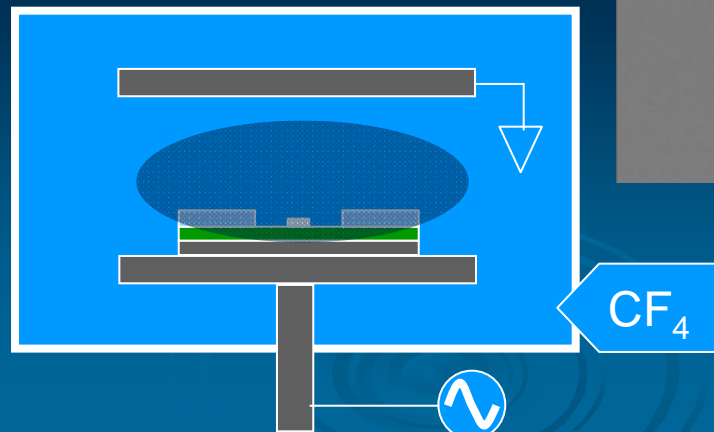
E-beam Lithography (EBL)



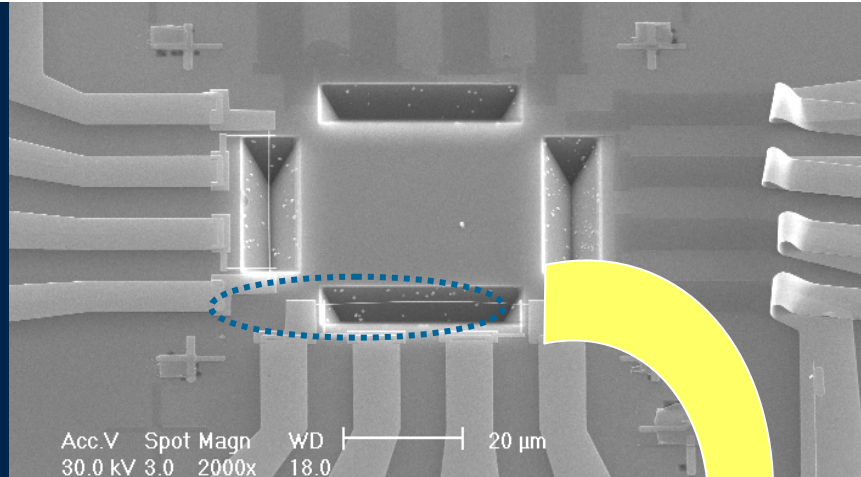
Dry Etching



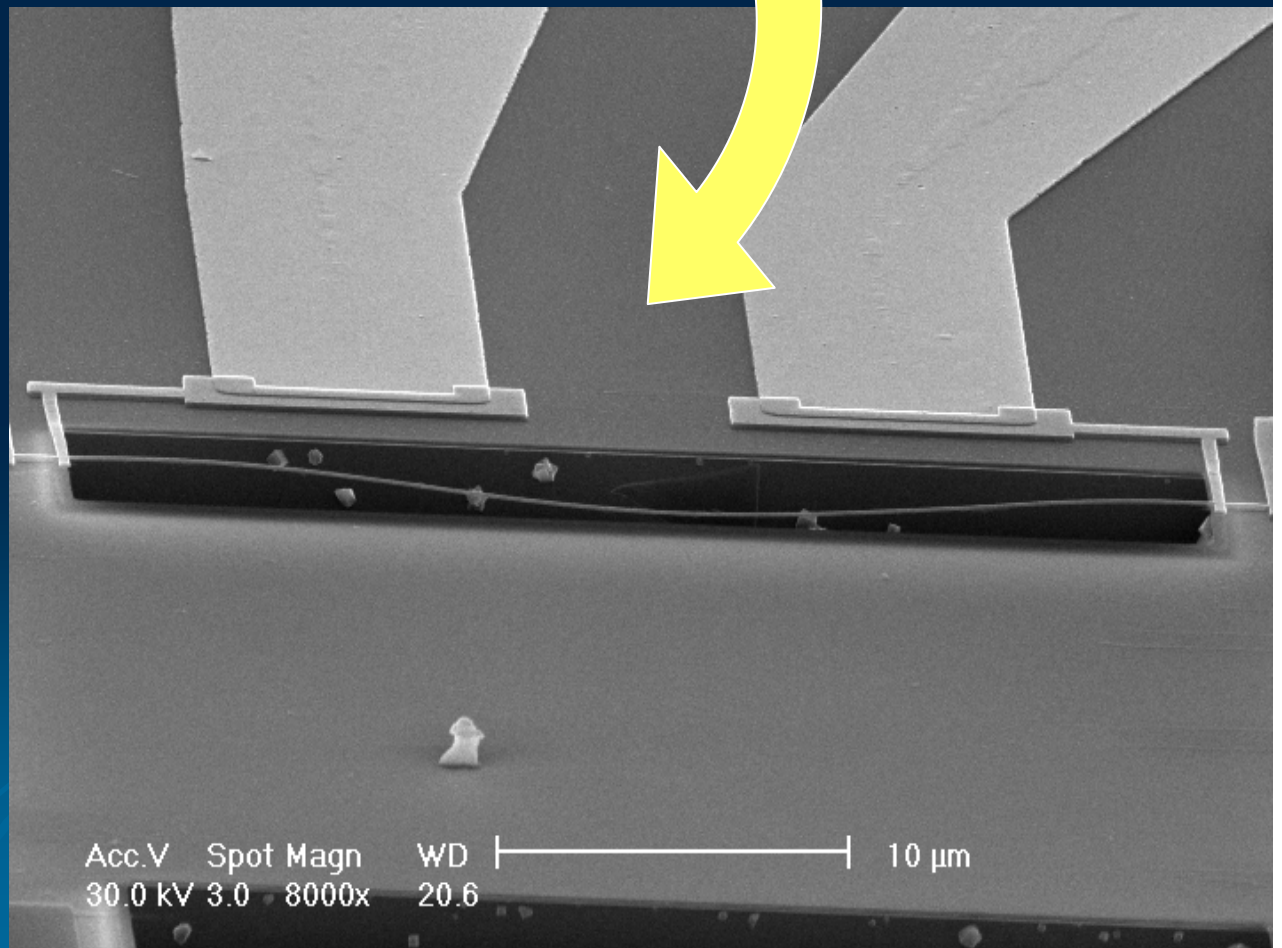
Reactive Ion Etching (RIE)



Wet Etching



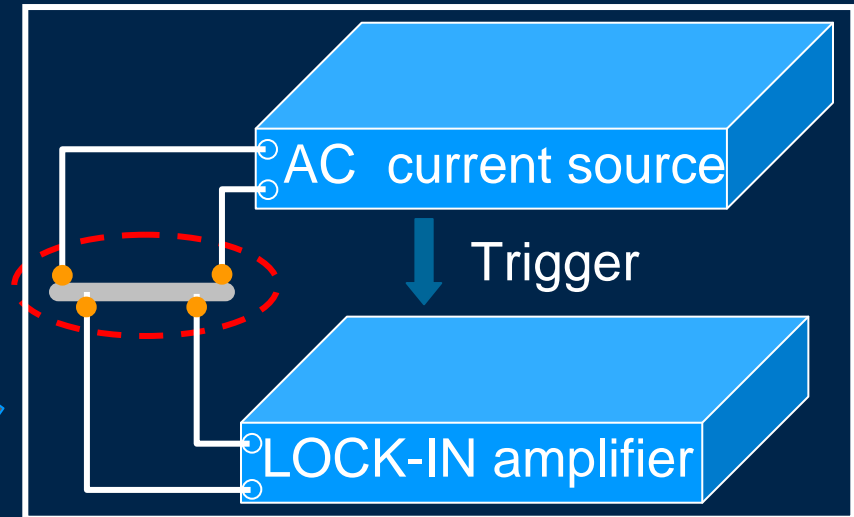
KOH
Wet etching



Method for single nanowire

Three requirements

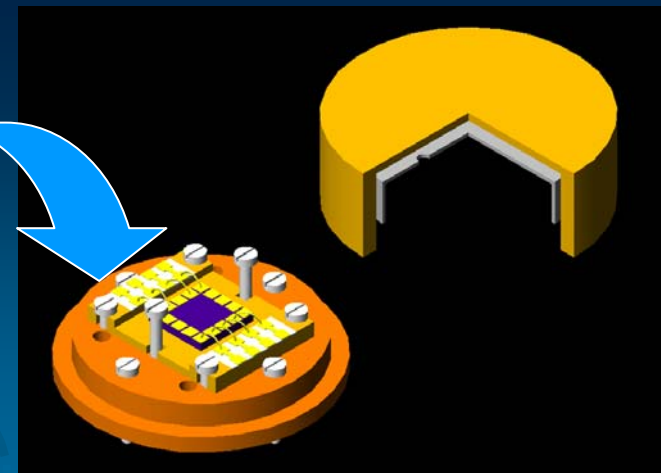
1. *Suspended*
2. *Highly thermal conductive to heat sink*
3. *Minimize the heat loss*



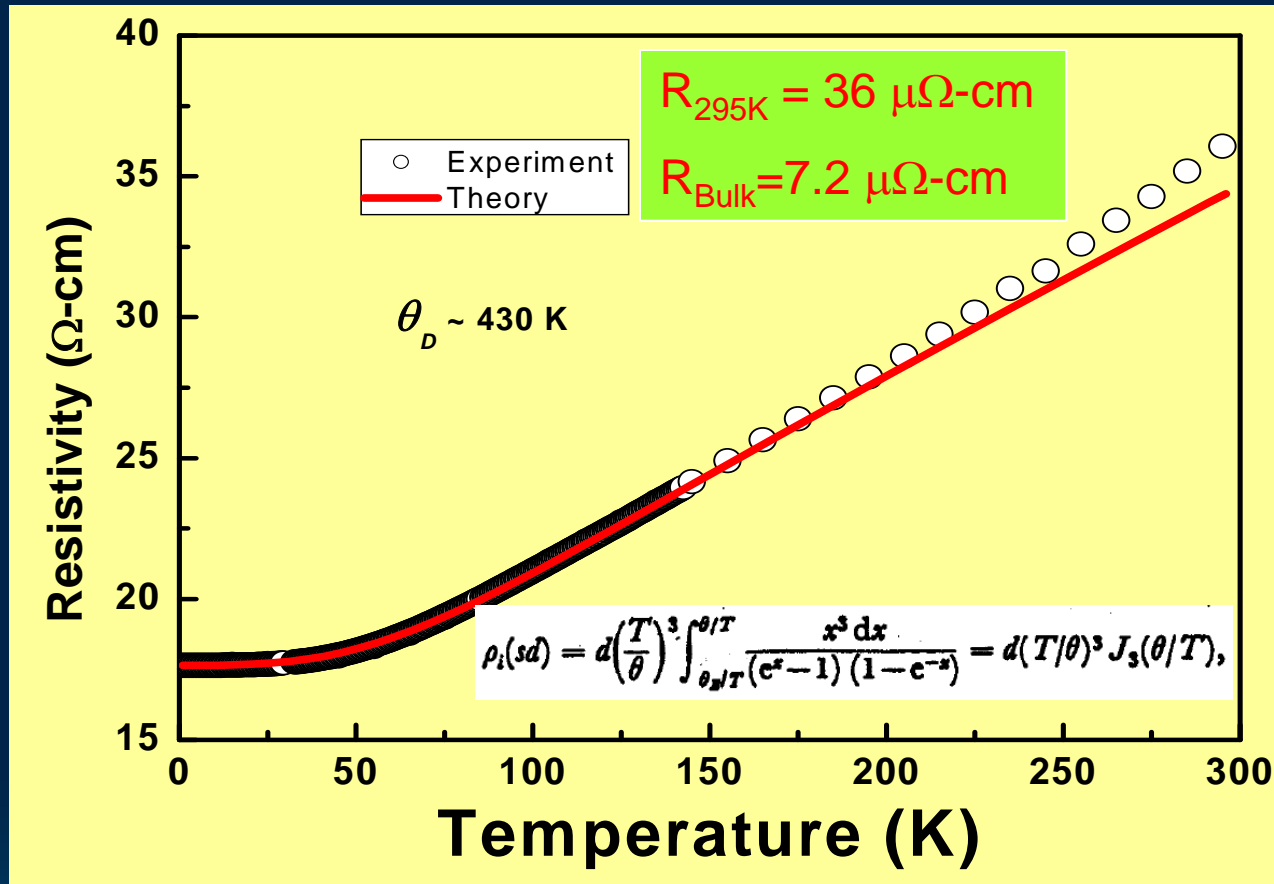
**Four-probe
measurement electrodes**

**Sapphire, Si
wafer**

Heat sink



Electrical Resistivity



Relative Resistance Ratio

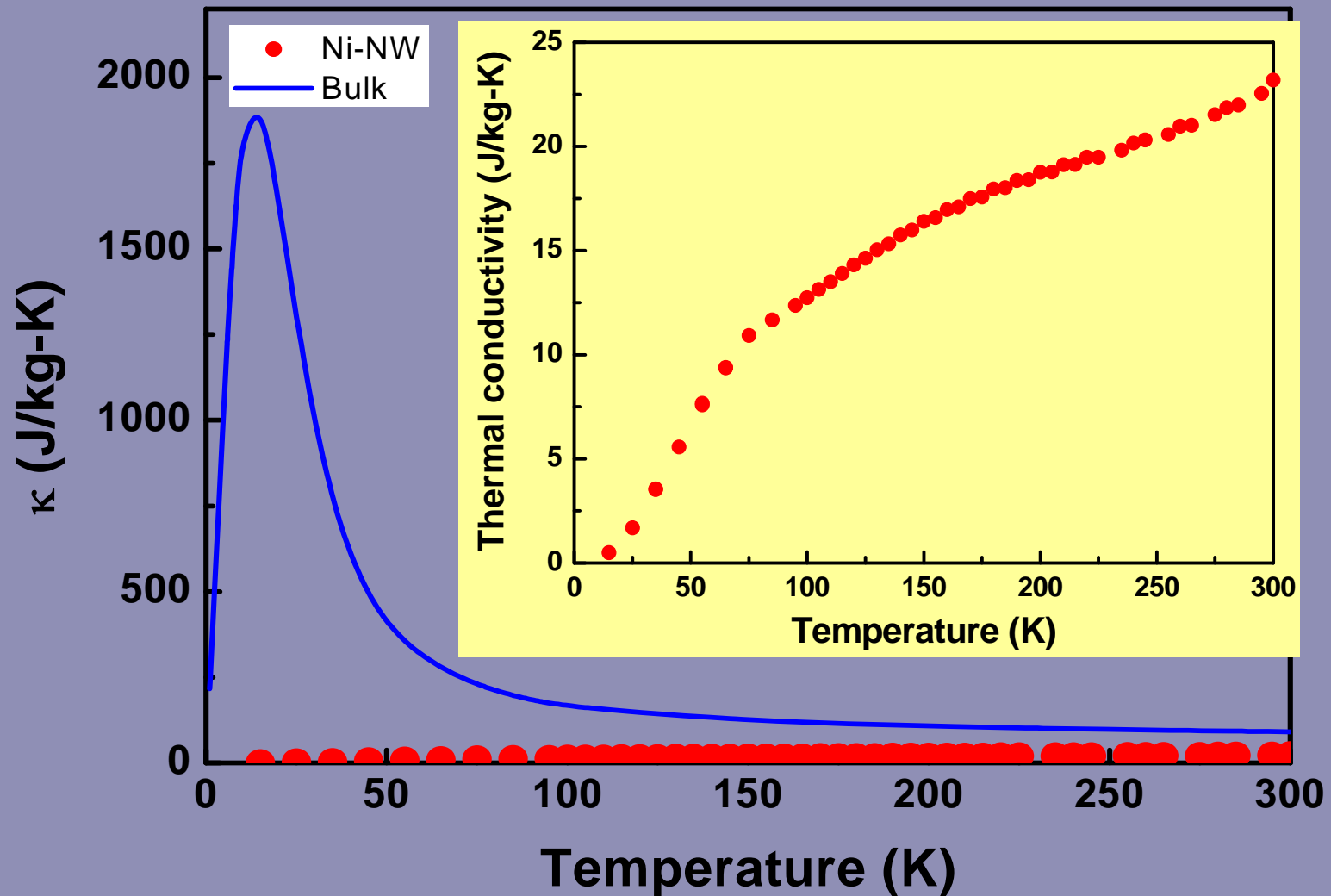
$$RRR_{295-15} \square 2.04$$

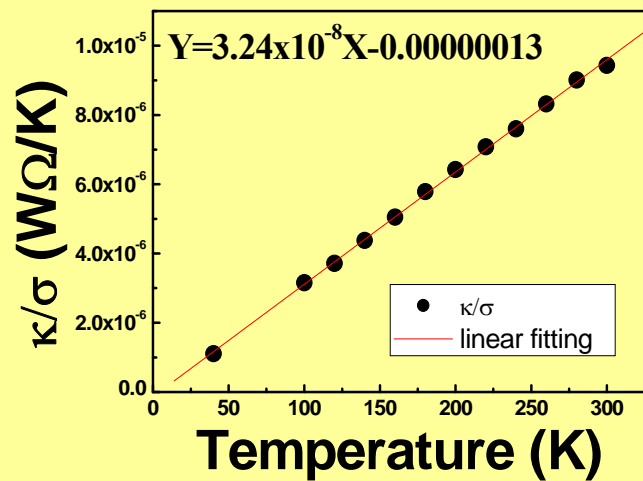
$$RRR_{\text{pure}} \square 47.4$$

TABLE 5. PHYSICAL DATA

element	structure	M	θ_D (°K)	$\frac{\rho M \theta_D^3}{T}$	λ_{295} (expt.) (W cm^{-1} deg^{-1})	λ_{295} (W cm^{-1} deg^{-1}) $= LT/\rho$	γ ($10^{-3} \text{ J/mole deg}^2$)
Fe	b.c.c.	55.85	400	0.7 \ddagger	0.82	0.73 ₈	5.0
Ru	h.c.p.	101.7	500	1.5	—	0.98 ₁	3.3
Os	h.c.p.	190.2	400	2.2	—	0.79 ₂	2.3
Co	h.c.p.	58.9	380	0.3 ₃ \ddagger	—	1.25	5.0
Rh	f.c.c.	102.9	350	0.5	1.51	1.51	4.9
Ir	f.c.c.	193.1	290	0.65	1.46	1.43	3.1
Ni	f.c.c.	58.7	390	0.45 \ddagger	0.91	1.03	7.0
Pd	f.c.c.	106.7	295	0.8	0.7	0.68 ₅	9.9
Pt	f.c.c.	195.2	225	0.8.	0.7	0.69.	6.7

Thermal Conductivity



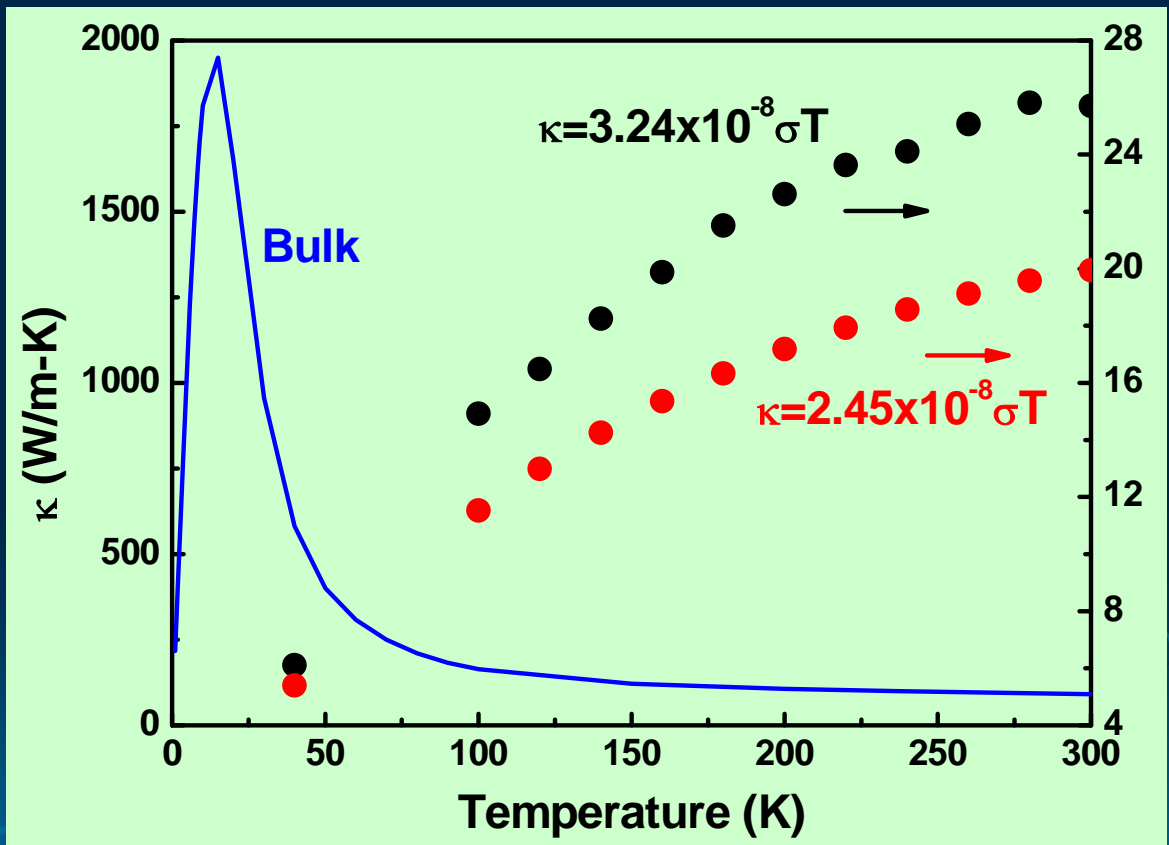


$$V_{3\omega} \approx \frac{4I^3 L R R'}{\pi^4 \kappa S \sqrt{1 + (2\omega\gamma)^2}}$$

Lorenz number L_0

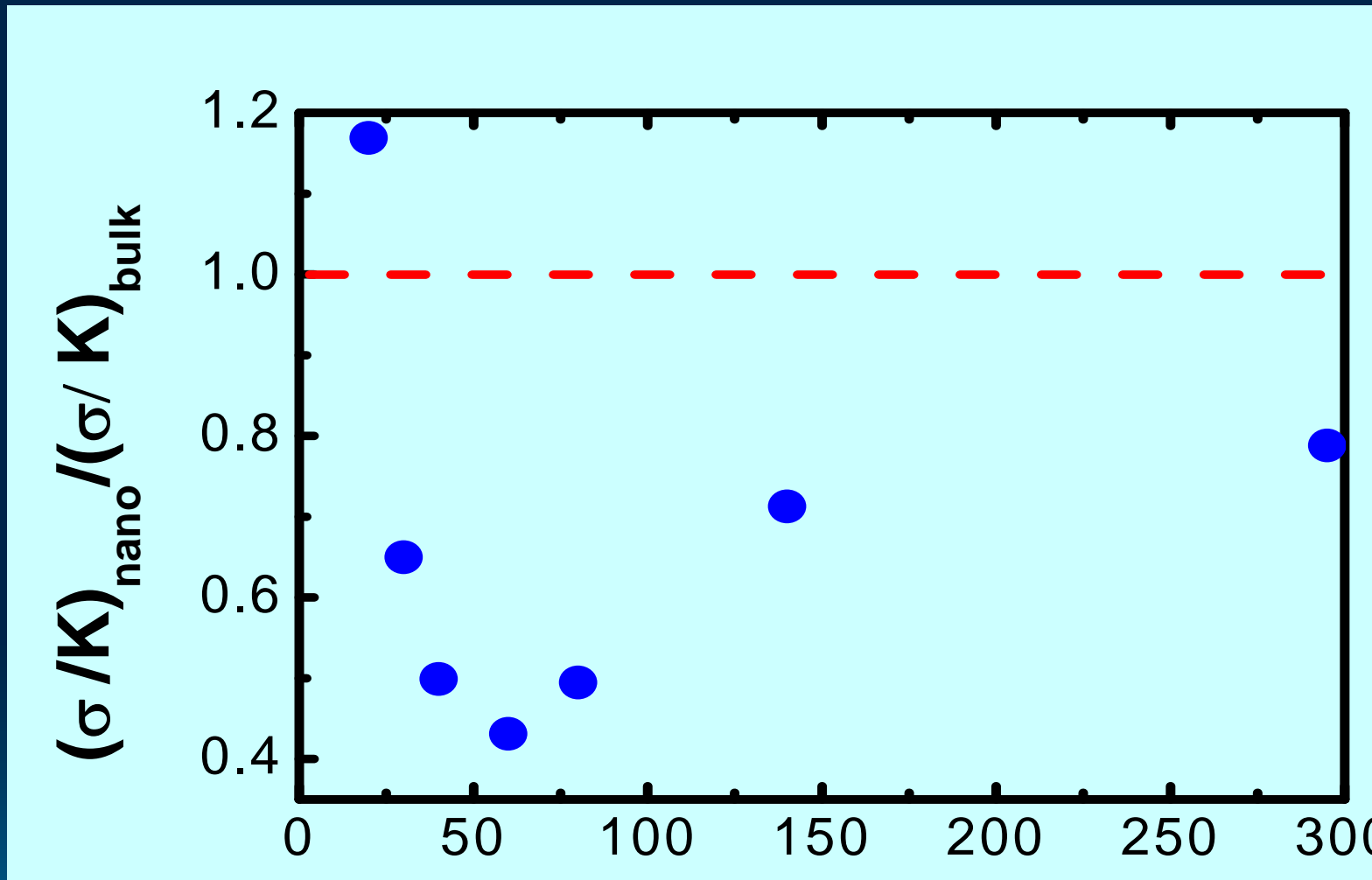
$$L_0 = \frac{\kappa}{\sigma T} = \frac{1}{3} \left(\frac{\pi k_B}{e} \right)^2$$

$$= 2.45 \times 10^{-8} \text{ W-}\Omega/\text{K}^2$$

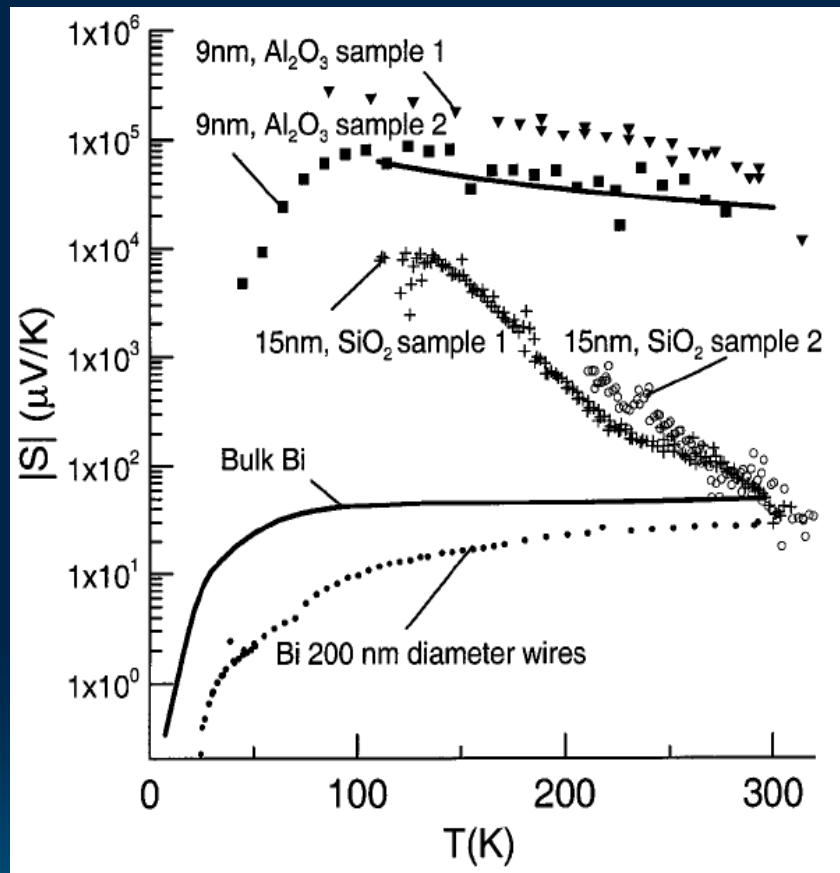


Wiedemann-Franz law $\kappa_e = \sigma L_0 T$

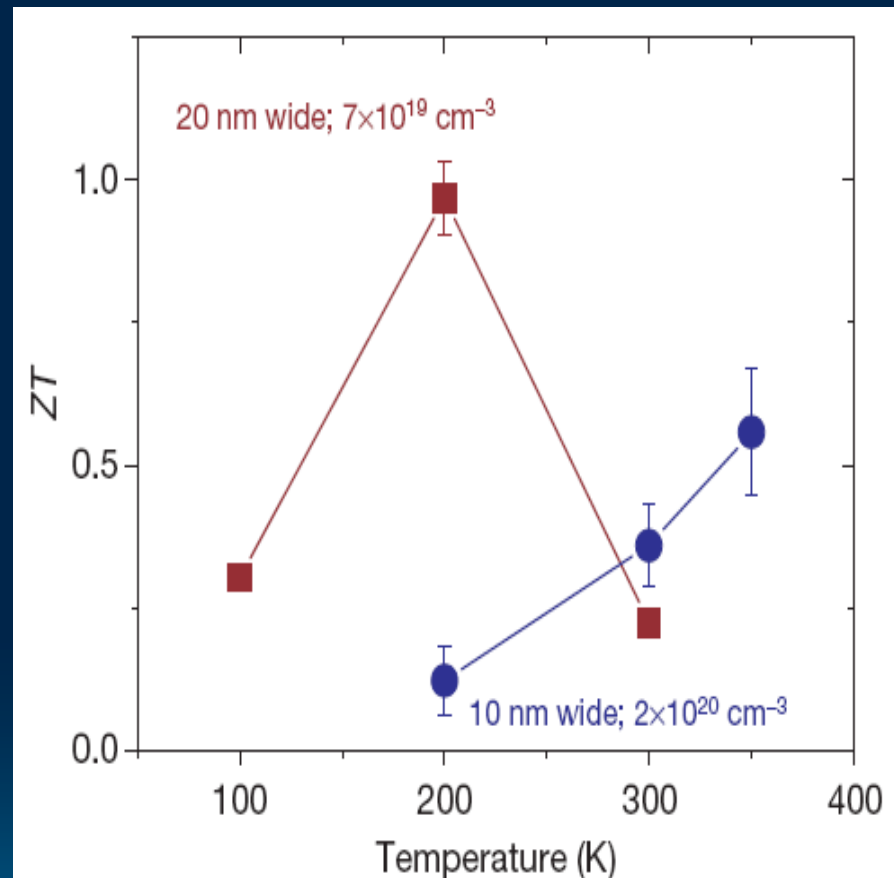
$ZT \propto \sigma/\kappa$ of Ni-nanowire vs. Bulk



Is the diameter in the quantum size regime? Need to make a smaller diameter wire ~ 10 nm?



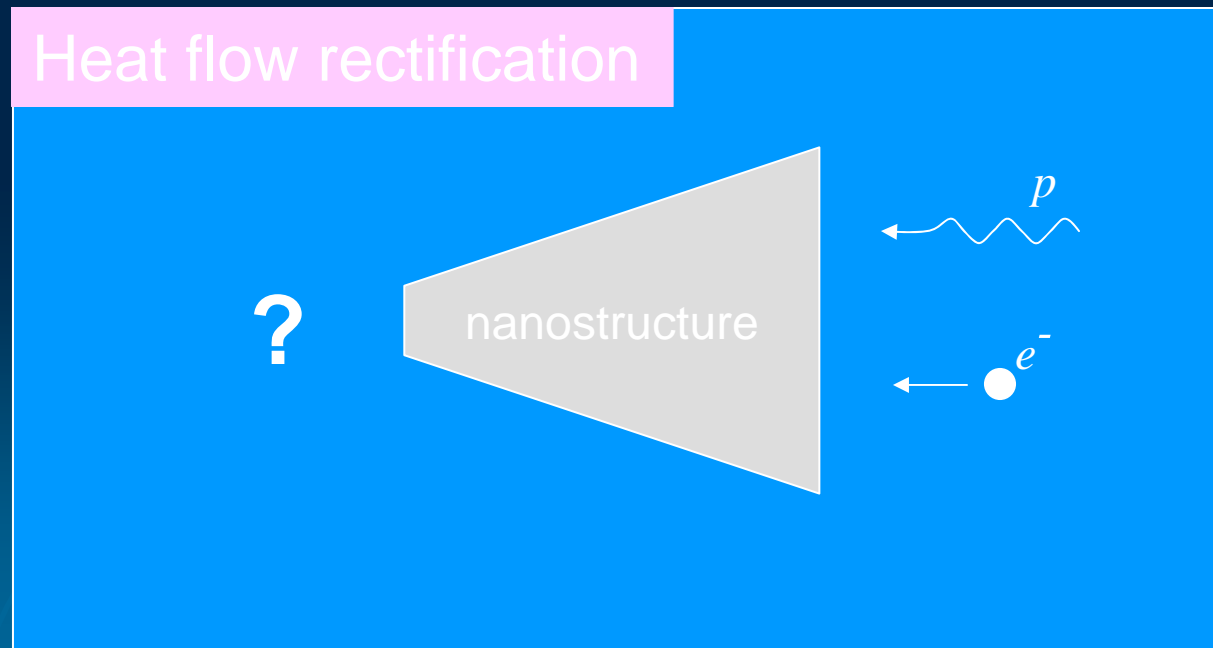
J.P. Heremans, et al., PRL **88**, 216801-1 (2002)

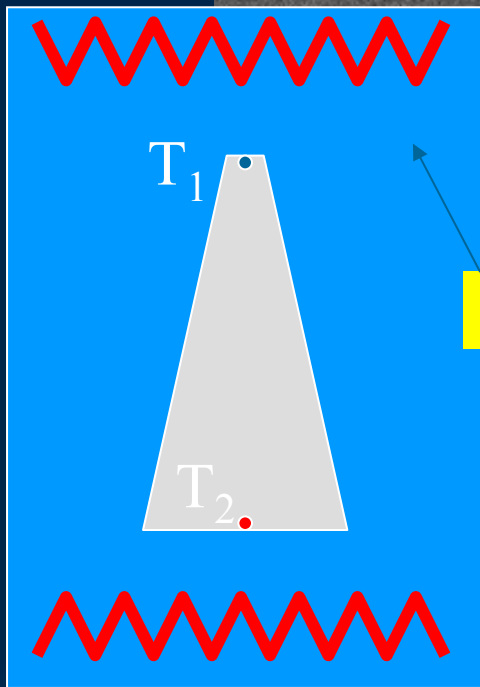


A.I. Boukai, et al., Nature **451**, 168 (2008)

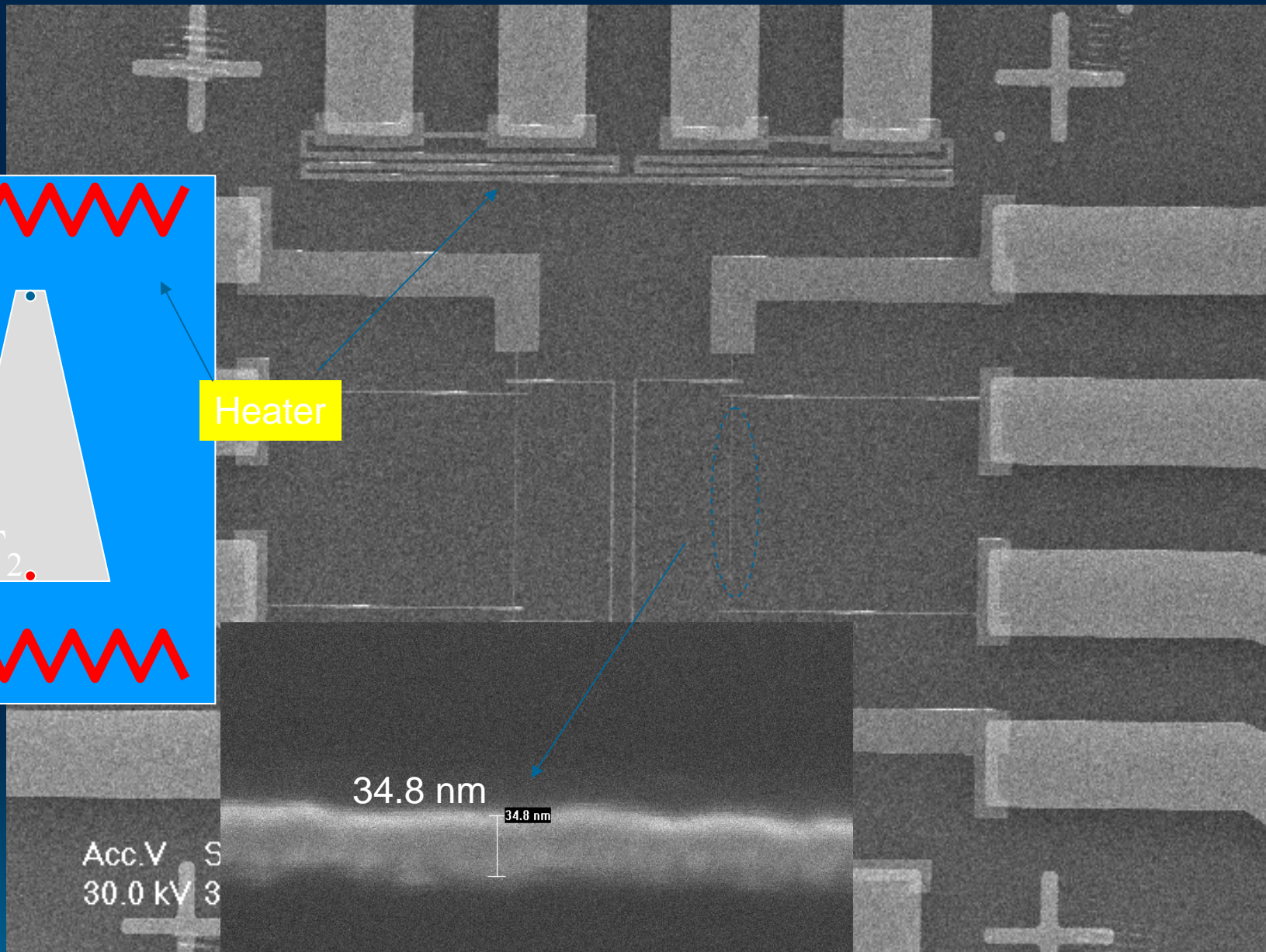
Nanostructures

- Transport properties-phonon, electron,...
 - Lattice structure □ disorder
 - Dimension □ Size effect
 - Spin dependence
 - **Shape**





Heater



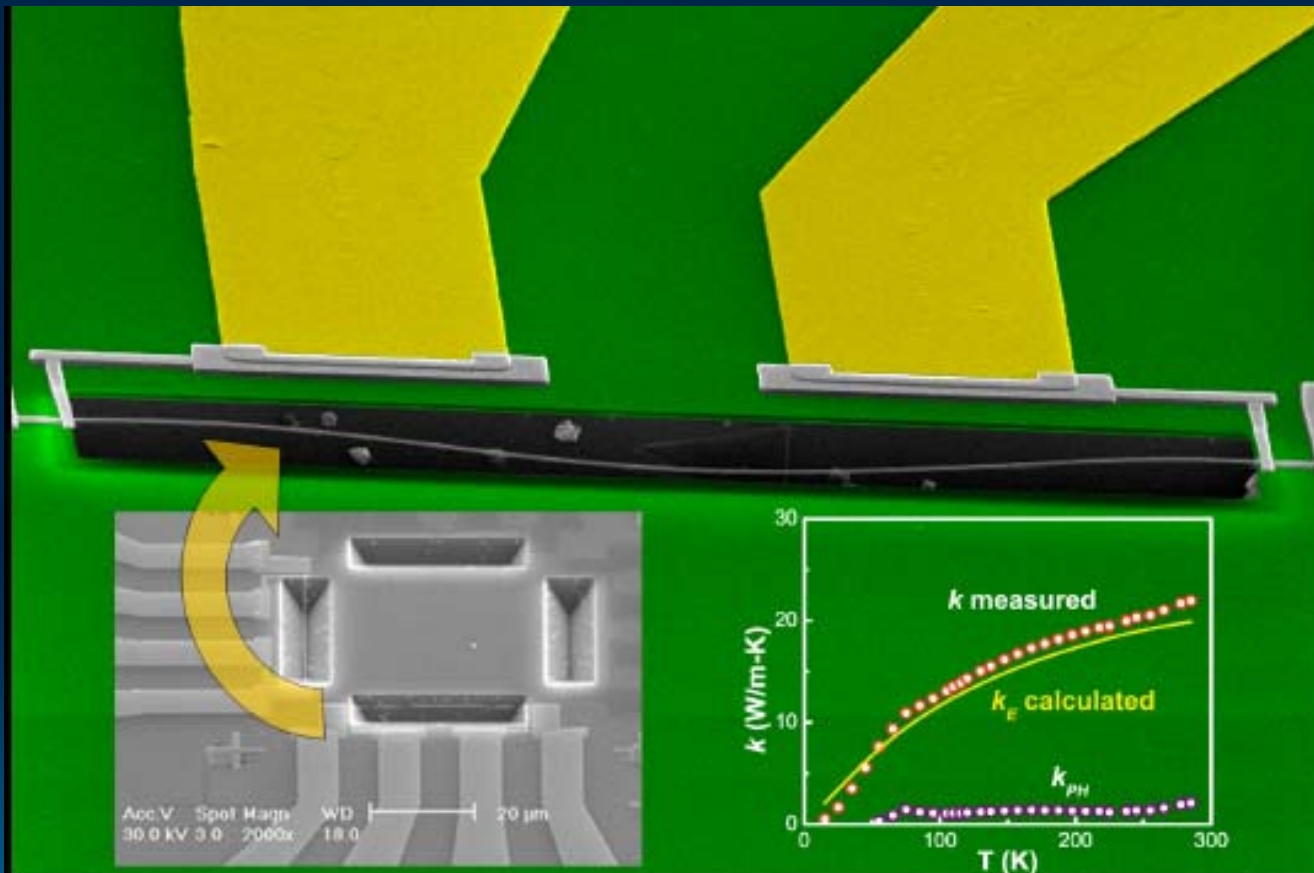
34.8 nm

34.8 nm

Acc.V S
30.0 kV 3

Acc.V Spot Magn WD | 100 nm
30.0 kV 3.0 800000x 4.2

**Thermo-power measurement on a suspended single
Ni-nanowire ($\Phi=200$ nm $L=10$ μm)
Results to appear in APL 2008 Febuary issue**



The graph was used on the Cover of APL 11 Feb issue

Summary

- ④ A lithographic process has been developed to construct the suspended structure.
- ④ The self-heating 3ω method and measurement system for nanoscale materials has been constructed.
- ④ The thermal conductivity and specific heat of diameter ~ 180 nm nickel wire are 23 W/m-K and 64.6 J/mol-K (at 25 $^{\circ}$ C), respectively.
- ④ A 30 nm nano-wire has been fabricated to demonstrate our capability